In the Claims

This listing of claims will replace all prior versions, and listings, of claims.

Listing of Claims

1. (Currently Amended): A reliability assessment system for assessing a reliability of a semiconductor product, comprising:

a web-based interface providing selections corresponding to assessment items, to receive a specific selection from the selections for the semiconductor product via a network, display a plurality of data items corresponding to the selected assessment item, wherein the selected assessment item has a specific number of the data items, and the data items are parameters used to assess the selected assessment item, receive a selection of at least one specific data item among the data items for the assessment item corresponding to the specific selection via the network, and receive input items corresponding to the data items without the specific data item via the network, wherein the respective assessment item comprises a manufacturing process for the semiconductor product; and

an assessment engine to perform a reliability assessment for the semiconductor product toward the assessment item corresponding to the selected specific selection according to the input items and the manufacturing process of the assessment item corresponding to the selected specific selection, generate a result of the reliability assessment, and display the result on the interface, wherein the result comprises at least one output

item for the specific data item of the assessment item corresponding to the selected specific selection.

- 2. (Cancelled).
- 3. (Original): The system of claim 1 wherein the assessment engine further writes the input items and the corresponding result to a database.
 - 4. (Original): The system of claim 1 further comprising an email server.
 - 5-7. (Cancelled).
- 8. (Previously Presented): The system of claim 7 wherein the process comprises GOI (gate oxide integrity), HCI (hot carrier injection), NBTI (negative bias temperature instability), EM (electromigration) or IMD(intermetal dielectirc)-TDDB (time dependent dielectric breakdown).
 - 9-10. (Cancelled).
- 11. (Previously Presented): The system of claim 1 wherein the assessment item comprises EFR (early failure rate), LTFR (long term failure rate), overdrive, overshoot, or temperature of the semiconductor product.

- 12. (Previously Presented): The system of claim 1 wherein the input items comprise technology and specifications of the semiconductor product.
 - 13. (Cancelled).
- 14. (Previously Presented): The system of claim 12 wherein the technology is geometry of the semiconductor product.
- 15. (Previously Presented): The system of claim 12 wherein the specification comprises parameters comprising at least a voltage and a lifetime of the semiconductor product.
- 16. (Currently Amended): A computerized reliability assessment method for assessing a reliability of a semiconductor product, comprising the steps of:
 - providing selections corresponding to assessment items by a web-based interface, wherein the respective assessment item comprises a manufacturing process for the semiconductor product;
 - receiving a specific selection from the selections for the semiconductor product via a network;
 - item, wherein the selected assessment item has a specific number of the data items, and the data items are parameters used to assess the selected assessment item;

- receiving a selection of at least one specific data item among the data items for the assessment item corresponding to the specific selection via the network;
- receiving input items corresponding to the data items without the specific data item via the network;
- performing a reliability assessment for the semiconductor product toward the assessment item corresponding to the selected specific selection according to the input items and the manufacturing process of the assessment item corresponding to the selected specific selection; and generating a result of the reliability assessment, wherein the result comprises at least one output item for the specific data item of the assessment item corresponding to the selected specific selection.
- 17. (Original): The method of claim 16 further comprising displaying the result on the web-based interface.
- 18. (Original): The method of claim 16 further comprising writing the input items and the corresponding result to a database.
- 19. (Original): The method of claim 16 further comprising sending an email notification.

20-22. (Cancelled).

23. (Previously Presented): The method of claim 22 wherein the process comprises GOI (gate oxide integrity), HCI (hot carrier injection), NBTI (negative bias temperature instability), EM (electromigration) or IMD(intermetal dielectirc)-TDDB (time dependent dielectric breakdown).

24-25. (Cancelled).

- 26. (Previously Presented): The method of claim 16 wherein the assessment item comprises EFR (early failure rate), LTFR (long term failure rate), overdrive, overshoot, or temperature of the semiconductor product.
- 27. (Previously Presented): The method of claim 16 wherein the input items comprise technology and specifications of the semiconductor product.
 - 28. (Cancelled).
- 29. (Previously Presented): The method of claim 27 wherein the technology is geometry of the semiconductor product.
- 30. (Previously Presented): The method of claim 27 wherein the specification comprises parameters comprising at least a voltage and a lifetime of the semiconductor product.

- 31. (Currently Amended): A machine-readable storage medium storing a computer program which, when executed, directs a computer to perform a method of reliability assessment for assessing a reliability of a semiconductor product, comprising the steps of:
 - providing selections corresponding to assessment items by a web-based interface, wherein the respective assessment item comprises a manufacturing process for the semiconductor product;
 - receiving a specific selection from the selections for the semiconductor product via a network;
 - item, wherein the selected assessment item has a specific number of the data items, and the data items are parameters used to assess the selected assessment item;
 - receiving a selection of at least one specific data item among the data items-for

 the assessment item corresponding to the specific selection via the

 network;
 - receiving input items corresponding to the data items without the specific data item via the network;
 - performing a reliability assessment for the semiconductor product toward the assessment item corresponding to the selected specific selection according to the input items and the manufacturing process of the assessment item corresponding to the selected specific selection; and

generating a result of the reliability assessment, wherein the result comprises at least one output item for the specific data item of the assessment item corresponding to the selected specific selection.

- 32. (Previously Presented): The storage medium of claim 31 wherein the method further comprises displaying the result on the web-based interface.
- 33. (Previously Presented): The storage medium of claim 31 wherein the method further comprises writing the input items and the corresponding result to a database.
- 34. (Previously Presented): The storage medium of claim 31 wherein the method further comprises sending an email notification.

35-37. (Cancelled).

38. (Previously Presented): The storage medium of claim 37 wherein the process comprises GOI (gate oxide integrity), HCI (hot carrier injection), NBTI (negative bias temperature instability), EM (electromigration) or IMD(intermetal dielectirc)-TDDB (time dependent dielectric breakdown).

39-40. (Cancelled).

- 41. (Previously Presented): The storage medium of claim 31 wherein the assessment item comprises EFR (early failure rate), LTFR (long term failure rate), overdrive, overshoot, or temperature of the semiconductor product.
- 42. (Previously Presented): The storage medium of claim 31 wherein the input items comprise technology and specifications of the semiconductor product.
 - 43. (Cancelled).
- 44. (Previously Presented): The storage medium of claim 42 wherein the technology is geometry of the semiconductor product.
- 45. (Previously Presented): The storage medium of claim 42 wherein the specification comprises parameters further comprising at least a voltage and a lifetime of the semiconductor product.

46-55. (Cancelled).